

## 1. Global joint venture starts operations as WeEn Semiconductors

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WeEn Semiconductors





### 1. General description

Planar passivated four quadrant triac in a SOT186A "full pack" plastic package intended for use in applications requiring high bidirectional transient and blocking voltage capability and high thermal cycling performance. Typical applications include motor control, industrial and domestic lighting, heating and static switching.

### 2. Features and benefits

- High blocking voltage capability
- High noise immunity
- Isolated package
- Planar passivated for voltage ruggedness and reliability
- Triggering in all four quadrants

### 3. Applications

- General purpose motor control
- General purpose switching

### 4. Quick reference data

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
V <sub>DRM</sub>	repetitive peak off- state voltage		-	-	600	V
I <sub>TSM</sub>	non-repetitive peak on- state current	full sine wave; $T_{j(init)}$ = 25 °C; $t_p$ = 20 ms; <u>Fig. 4</u> ; <u>Fig. 5</u>	-	-	155	A
I <sub>T(RMS)</sub>	RMS on-state current	full sine wave; $T_h \le 38$ °C; Fig. 1; Fig. 2; Fig. 3	-	-	16	A
Static charac	cteristics		·			
I <sub>GT</sub>	gate trigger current	V <sub>D</sub> = 12 V; I <sub>T</sub> = 0.1 A; T2+ G+; T <sub>j</sub> = 25 °C; <u>Fig. 7</u>	-	5	35	mA
		V <sub>D</sub> = 12 V; I <sub>T</sub> = 0.1 A; T2+ G-; T <sub>j</sub> = 25 °C; <u>Fig. 7</u>	-	8	35	mA
		V <sub>D</sub> = 12 V; I <sub>T</sub> = 0.1 A; T2- G-; T <sub>j</sub> = 25 °C; <u>Fig. 7</u>	-	10	35	mA





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Symbol	Parameter	Conditions	Min	Тур	Max	Unit
		V <sub>D</sub> = 12 V; I <sub>T</sub> = 0.1 A; T2- G+; T <sub>j</sub> = 25 °C; <u>Fig. 7</u>	-	22	70	mA

# 5. Pinning information

Table 2.	Pinning	information		
Pin	Symbol	Description	Simplified outline	Graphic symbol
1	T1	main terminal 1	mb	T2-T1
2	T2	main terminal 2		sym051
3	G	gate		·
mb	n.c.	mounting base; isolated		
			TO-220F (SOT186A)	

## 6. Ordering information

#### Table 3.Ordering information

Type number	Package		
	Name	Description	Version
BT139X-600	TO-220F	plastic single-ended package; isolated heatsink mounted; 1 mounting hole; 3-lead TO-220 "full pack"	SOT186A

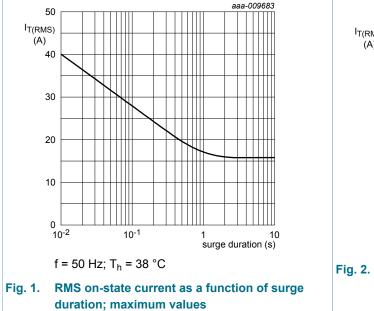
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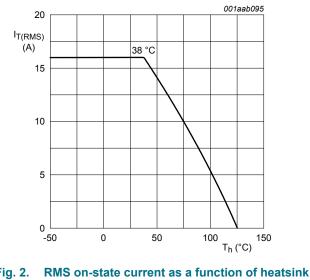
### 7. Limiting values

#### Table 4.Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

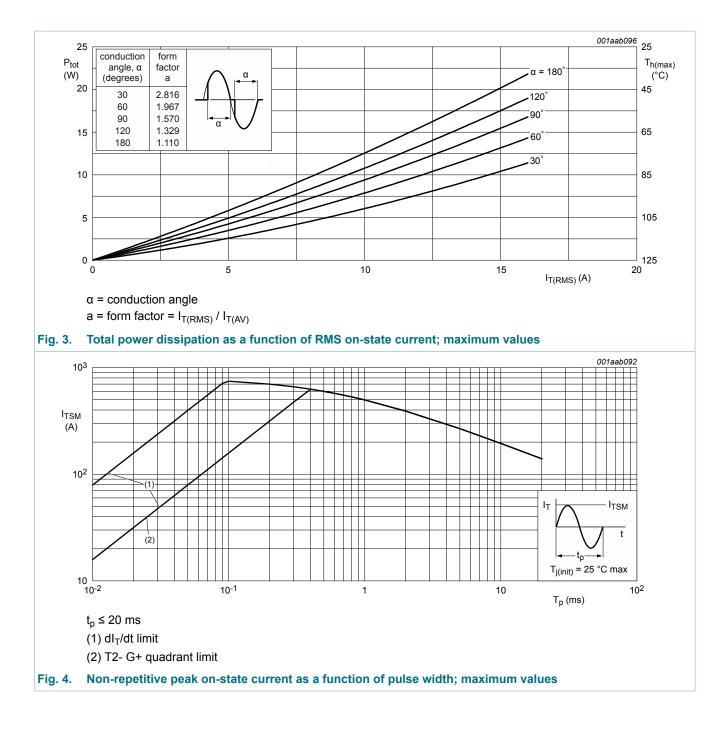
Symbol	Parameter	Conditions	Min	Max	Unit
V <sub>DRM</sub>	repetitive peak off-state voltage		-	600	V
I <sub>T(RMS)</sub>	RMS on-state current	full sine wave; T <sub>h</sub> ≤ 38 °C; <u>Fig. 1; Fig. 2;</u> <u>Fig. 3</u>	-	16	А
I <sub>TSM</sub>	non-repetitive peak on-state current	full sine wave; T <sub>j(init)</sub> = 25 °C; t <sub>p</sub> = 20 ms; <u>Fig. 4; Fig. 5</u>	-	155	A
		full sine wave; $T_{j(init)} = 25 \text{ °C};$ $t_p = 16.7 \text{ ms}$	-	170	А
l <sup>2</sup> t	I2t for fusing	t <sub>p</sub> = 10 ms; SIN	-	120	A <sup>2</sup> s
dl <sub>T</sub> /dt	rate of rise of on-state current	I <sub>G</sub> = 70 mA; T2+ G+	-	50	A/µs
		I <sub>G</sub> = 70 mA; T2+ G-	-	50	A/µs
		I <sub>G</sub> = 140 mA; T2- G+	-	10	A/µs
		I <sub>G</sub> = 70 mA; T2- G-	-	50	A/µs
I <sub>GM</sub>	peak gate current		-	2	А
P <sub>GM</sub>	peak gate power		-	5	W
P <sub>G(AV)</sub>	average gate power	over any 20 ms period	-	0.5	W
T <sub>stg</sub>	storage temperature		-40	150	°C
Tj	junction temperature		-	125	°C





temperature; maximum values

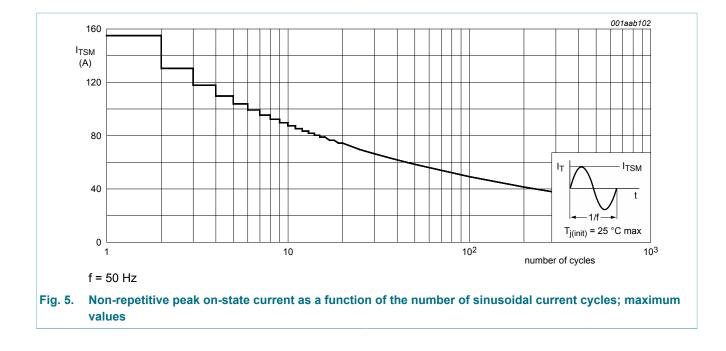
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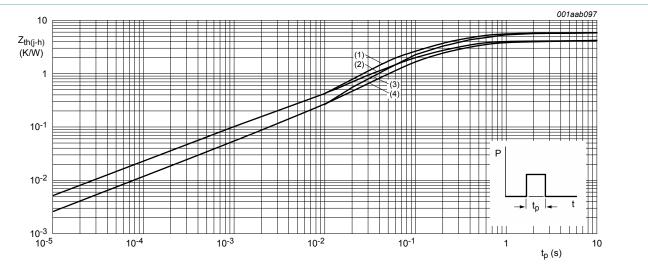
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## 8. Thermal characteristics

Table 5. The	ermal characteristics					
Symbol	Parameter	Conditions	Min	Тур	Мах	Unit
R <sub>th(j-h)</sub>	thermal resistance from junction to	full or half cycle with heatsink compound; Fig. 6	-	-	4	K/W
	heatsink	full or half cycle without heatsink compound; Fig. 6	-	-	5.5	K/W
R <sub>th(j-a)</sub>	thermal resistance from junction to ambient	in free air	-	55	-	K/W



(1) Unidirectional (half cycle) without heatsink compound

(2) Unidirectional (half cycle) with heatsink compound

(3) Bidirectional (full cycle) without heatsink compound

(4) Bidirectional (full cycle) with heatsink compound

Fig. 6. Transient thermal impedance from junction to heatsink as a function of pulse width

# 9. Isolation characteristics

Table 6. Isol	ation characteristics					
Symbol	Parameter	Conditions	Min	Тур	Max	Unit
V <sub>isol(RMS)</sub>	RMS isolation voltage	from all terminals to external heatsink; sinusoidal waveform; clean and dust free; 50 Hz $\leq$ f $\leq$ 60 Hz; RH $\leq$ 65 %; T <sub>h</sub> = 25 °C	-	-	2500	V
C <sub>isol</sub>	isolation capacitance	from main terminal 2 to external heatsink; f = 1 MHz; T <sub>h</sub> = 25 °C	-	10	-	pF

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## **10. Characteristics**

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
Static chara	cteristics					
I <sub>GT</sub>	gate trigger current	V <sub>D</sub> = 12 V; I <sub>T</sub> = 0.1 A; T2+ G+; T <sub>j</sub> = 25 °C; <u>Fig. 7</u>	-	5	35	mA
		V <sub>D</sub> = 12 V; I <sub>T</sub> = 0.1 A; T2+ G-; T <sub>j</sub> = 25 °C; <u>Fig. 7</u>	-	8	35	mA
		V <sub>D</sub> = 12 V; I <sub>T</sub> = 0.1 A; T2- G-; T <sub>j</sub> = 25 °C; <u>Fig. 7</u>	-	10	35	mA
		V <sub>D</sub> = 12 V; I <sub>T</sub> = 0.1 A; T2- G+; T <sub>j</sub> = 25 °C; <u>Fig. 7</u>	-	22	70	mA
L	latching current	V <sub>D</sub> = 12 V; I <sub>G</sub> = 0.1 A; T2+ G+; T <sub>j</sub> = 25 °C; <u>Fig. 8</u>	-	7	40	mA
		V <sub>D</sub> = 12 V; I <sub>G</sub> = 0.1 A; T2+ G-; T <sub>j</sub> = 25 °C; <u>Fig. 8</u>	-	20	60	mA
		V <sub>D</sub> = 12 V; I <sub>G</sub> = 0.1 A; T2- G-; T <sub>j</sub> = 25 °C; <u>Fig. 8</u>	-	8	40	mA
		V <sub>D</sub> = 12 V; I <sub>G</sub> = 0.1 A; T2- G+; T <sub>j</sub> = 25 °C; <u>Fig. 8</u>	-	10	60	mA
I <sub>H</sub>	holding current	V <sub>D</sub> = 12 V; T <sub>j</sub> = 25 °C; <u>Fig. 9</u>	-	6	45	mA
V <sub>T</sub>	on-state voltage	I <sub>T</sub> = 20 A; T <sub>j</sub> = 25 °C; <u>Fig. 10</u>	-	1.2	1.6	V
V <sub>GT</sub>	gate trigger voltage	V <sub>D</sub> = 12 V; I <sub>T</sub> = 0.1 A; T <sub>j</sub> = 25 °C; Fig. 11	-	0.7	1	V
		V <sub>D</sub> = 400 V; I <sub>T</sub> = 0.1 A; T <sub>j</sub> = 125 °C; Fig. 11	0.25	0.4	-	V
D	off-state current	V <sub>D</sub> = 600 V; T <sub>j</sub> = 125 °C	-	0.1	0.5	mA
Dynamic ch	aracteristics	II				
dV <sub>D</sub> /dt	rate of rise of off-state voltage	$V_{DM}$ = 402 V; T <sub>j</sub> = 125 °C; (V <sub>DM</sub> = 67% of V <sub>DRM</sub> ); exponential waveform; gate open circuit	200	250	-	V/µs
dV <sub>com</sub> /dt	rate of change of commutating voltage	$V_D$ = 400 V; T <sub>j</sub> = 95 °C; dI <sub>com</sub> /dt = 7.2 A/ ms; I <sub>T</sub> = 16 A; gate open circuit	10	20	-	V/µs
t <sub>gt</sub>	gate-controlled turn-on time	I <sub>TM</sub> = 20 A; V <sub>D</sub> = 600 V; I <sub>G</sub> = 0.1 A; dI <sub>G</sub> / dt = 5 A/μs	-	2	-	μs

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# BT139X-600

001aab100

100 Tj (°C) 150

001aab094

3

V<sub>T</sub> (V)

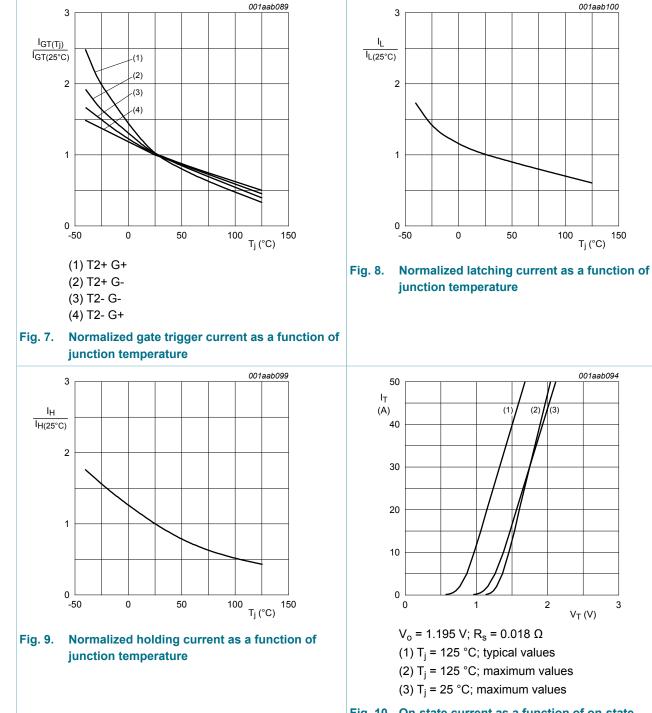
50

(1)

(2) (3)

2

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#### Fig. 10. On-state current as a function of on-state voltage

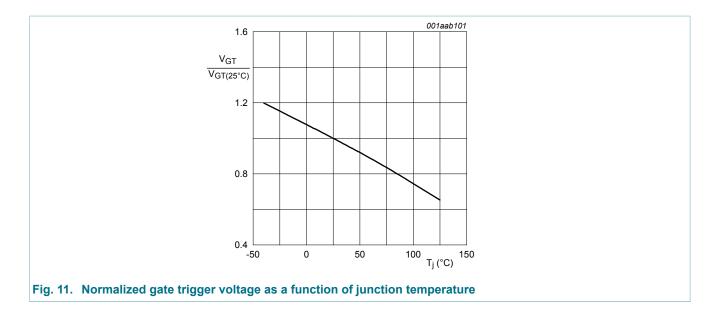
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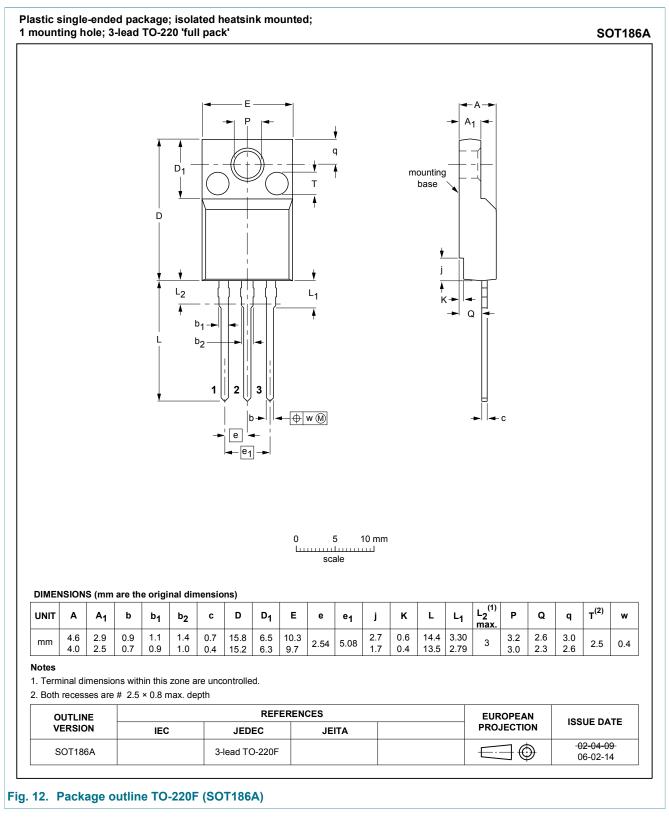
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### **11. Package outline**



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Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
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